

Type	L #	Hits	Search Text	DBs	Time Stamp
2 BRS	L1	1	6297104.pn.	USPAT; CN-EGI UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:43
3 BRS	L2	1	6840692.pn. or 6150243.pn.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:46
3 BRS	L3	2984	(logic adjl device) and (memory adjl device)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:47
4 BRS	L4	44	latest adjl transistors; near-IG (dielectric adjl layer)	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:55
5 BRS	L5	4	3 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:51

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6	BRS	L6	149	(first adj1 transistor) near15 'dielectric adj1 layer'	USPAT; US-PGP; UB; EPO; JPO; 2002/03/14 DERWEN; 1: T; IBM_TD; B	2002/03/14 21:56
7	BRS	L7	4	3 and 6	USPAT; US-PGP; UB; EPO; JPO; 2002/03/28 DERWEN; 21:56 T; IBM_TD; B	2002/03/28 21:56
8	BRS	L8	16	3 sides (first adj1 transistor near15 'dielectric adj1 layer')	USPAT; US-PGP; UB; EPO; JPO; 2002/03/28 DERWEN; 22:36 T; IBM_TD; B	2002/03/28 22:36
9	BRS	L9	79	3 and 8	USPAT; US-PGP; UB; EPO; JPO; 2002/03/28 DERWEN; 21:57 T; IBM_TD; B	2002/03/28 21:57
10	BRS	L10	69	9 and thickness	USPAT; US-PGP; UB; EPO; JPO; 2002/03/28 DERWEN; 21:57 T; IBM_TD; B	2002/03/28 21:57

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11	BRS	L11	37	10 and channel adj1 region	USPAT; US-PPG; UB; EPO; JPO; DERWEN	2002/03/28 21:58
11	BRS	L12	13	11 and oxidation	USPAT; US-PPG; UB; EPO; JPO; DERWEN	2002/03/28 21:58
11	BRS	L13	35	11 and oxid\$4	USPAT; US-PPG; UB; EPO; JPO; DERWEN	2002/03/28 22:15
11	BRS	L14	17000	transistor pair (electrostatic adj1 layer or silicon adj1 dioxide)	USPAT; US-PPG; UB; EPO; JPO; DERWEN	2002/03/28 22:46
11	BRS	L15	114	13 and 14	USPAT; US-PPG; UB; EPO; JPO; DERWEN	2002/03/28 22:46

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					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	
16	BRS	L16	100	15 and channel		2002/03/28 22:47
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	
17	BRS	L17	189	16 and (source and drain)		2002/03/28 23:17
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	
18	BRS	L18	407	3 and gate nearl oxide\$1		2002/03/28 23:18
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	
19	BRS	L19	389	18 and transistor		2002/03/28 23:18
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L21	288	20 and channel	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TDB; B	2002/03/28 23:14
22	BRS	L22	258	21 and (source and drain)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TDB; B	2002/03/28 23:14
23	BRS	L23	129	22 and oxidation	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TDB; B	2002/03/28 23:14
24	BRS	L24	258	22 and oxid\$4	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TDB; B	2002/03/28 23:55
				22 and oxid\$4	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TDB; B	2002/03/28 23:55

	Type	L #	Hits	Search Text	DBs	Time Stamp
					USPAT; US-FOU UB; EPO; JPO; DERWEN; T; IBM_TD B	
3/27	PRS	L27	0	(silicon adj1 dioxide and silicon adj1 nitride) near10 (high adj1 oxidation)	USPAT; US-FOU UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/27 00:47
3/28	PRS	L28	128	silicon adj1 dioxide near10 silicon adj1 nitride) near10 (oxidation)	USPAT; US-FOU UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/28 00:49
3/29	PRS	L29	1	3 and 28	USPAT; US-FOU UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/29 00:51
3/30	PRS	L30	191	28 and transistor	USPAT; US-FOU UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/29 00:53

	Type	L #	Hits	Search Text	DBs	Time Stamp
1.	BRS	131	182	30 and high	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/29 00:54
2.	BRS	132	114	31 and (memory and logic)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/29 00:54
3.0	BRS	132	42	31 and (memory or logic)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/29 01:03